





25V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = +25°C	
25V	4Ω @ V _{GS} = 4.5V	0.32A	
250	5Ω @ V _{GS} = 2.7V	0.28A	

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load switch
- Portable applications
- **Power Management Functions**

Features

- 0.4mm ultra low profile package for thin application
- 0.48mm² package footprint, 16 times smaller than SOT23
- Low V_{GS(th)}, can be driven directly from a battery
- Low R_{DS(on)}
- ESD Protected Gate (>6kV Human Body Mode)
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

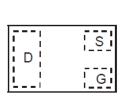
- Case: X2-DFN0806-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.00043 grams (approximate)



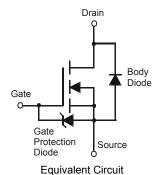
X2-DFN0806-3



Bottom View



Top View Package Pin Configuration



Ordering Information (Note 4)

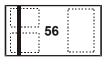
Ī	Part Number	Compliance	Case	Packaging
	DMN25D0UFA-7B	Standard	X2-DFN0806-3	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and 4.1000ppm antimony compounds.
 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

DMN25D0UFA-7B



Top View Bar Denotes Gate and Source Side

56 = Product Type Marking Code



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	25	V
Gate-Source Voltage		V_{GSS}	V _{GSS} 8	
	(Note 6)	,	0.32	А
Continuous Drain Current, V _{GS} = 4.5V	$T_A = +70^{\circ}C \text{ (Note 6)}$	ID	0.25	
	(Note 5)	ID	0.24	Α
Pulsed Drain Current	(Note 7)	I _{DM}	1.2	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 6)	Б	0.63	- W	
Power Dissipation	(Note 5)	P _D	0.28		
Thermal Resistance, Junction to Ambient	(Note 6)	Б	201	°C/W	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	338		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

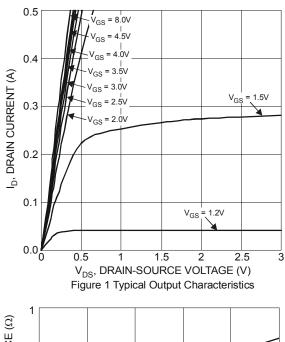
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	25	_	_	V	V _{GS} = 0V, I _D = 250μA	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	V _{DS} = 20V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	100	nA	V _{GS} = 8V, V _{DS} = 0V	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(th)}	0.6	_	1.2	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	Б	_	_	4	Ω	V _{GS} = 4.5V, I _D = 0.4A	
Static Drain-Source On-Resistance	R _{DS(on)}	_	_	5	12	V _{GS} = 2.7V, I _D = 0.2A	
Forward Transfer Admittance	Y _{fs}	_	1	-	S	$V_{DS} = 5V, I_D = 0.4A$	
Diode Forward Voltage	V _{SD}	_	0.76	1.2	V	V _{GS} = 0V, I _S = 0.29A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	27.9	_	pF		
Output Capacitance	Coss	_	6.1	_	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	2	_	pF		
Gate Resistance	Rg	_	26.4	_	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz	
Total Gate Charge	Qg	_	0.36	_	nC		
Gate-Source Charge	Qgs	_	0.06	_	nC	$V_{DS} = 5V, V_{GS} = 4.5V,$	
Gate-Drain Charge	Q _{gd}	_	0.04	_	nC	$I_D = 0.2A$	
Turn-On Delay Time	t _{D(on)}	_	2.9	_	ns		
Turn-On Rise Time	t _r	_	1.8	_	ns	$V_{DS} = 6V$, $V_{GS} = 4.5V$, $I_{D} = 0.5A$, $R_{G} = 50\Omega$	
Turn-Off Delay Time	t _{D(off)}	_	6.6	_	ns		
Turn-Off Fall Time	t _f	_	2.3	_	ns		

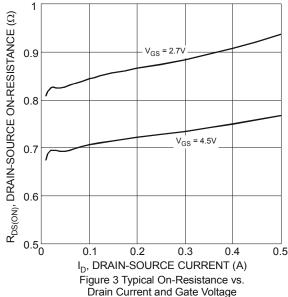
Notes:

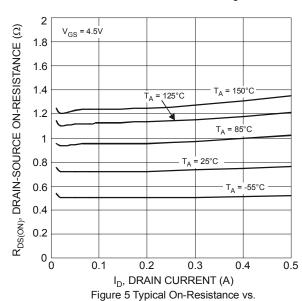
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 Short duration pulse test used to minimize self-heating effect.

- 8. Guaranteed by design. Not subject to production testing.

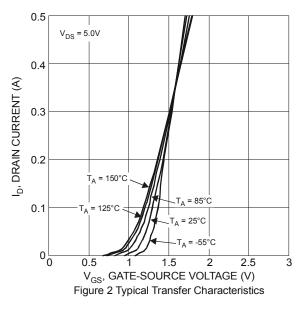


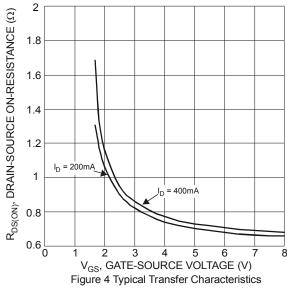


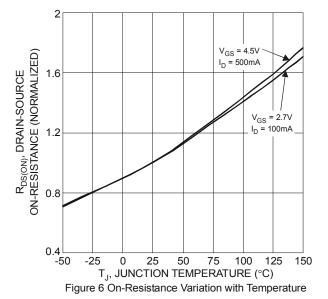




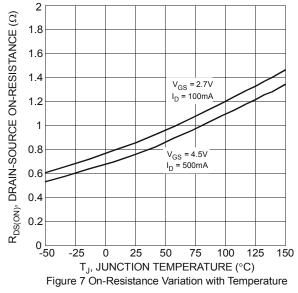
Drain Current and Temperature

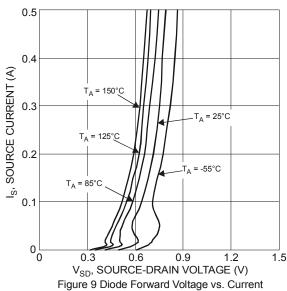


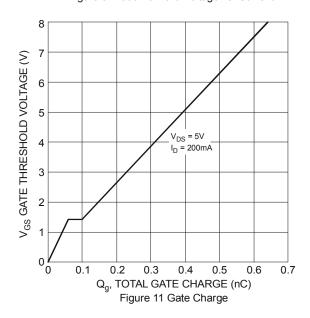












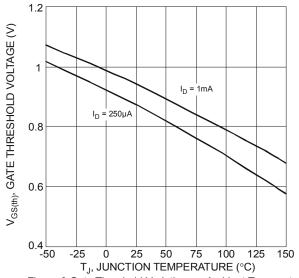
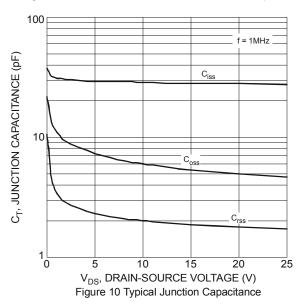
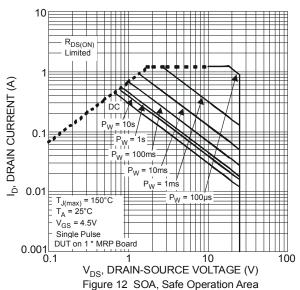
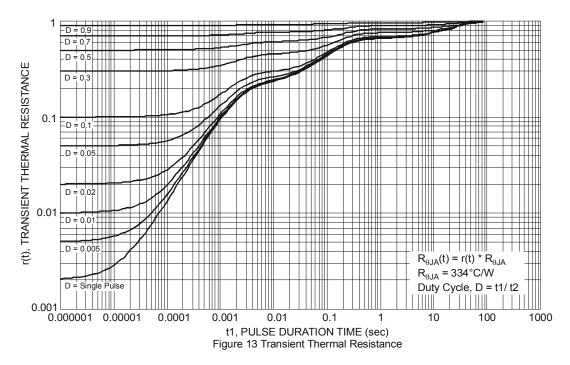


Figure 8 Gate Threshold Variation vs. Ambient Temperature



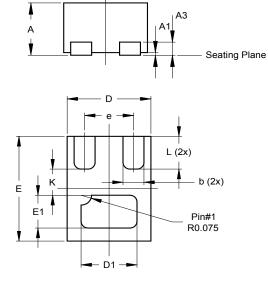






Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

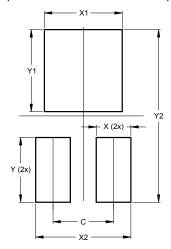


X2-DFN0806-3					
Dim	Min	Max	Тур		
Α	0.375	0.40	0.39		
A1	0	0.05	0.02		
A3	-	-	0.10		
b	0.10	0.20	0.15		
D	0.55	0.65	0.60		
D1	0.35	0.45	0.40		
E	0.75	0.85	0.80		
E1	0.20	0.30	0.25		
е	-	-	0.35		
K	-	-	0.20		
L	0.20	0.30	0.25		
All Dimensions in mm					



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
С	0.350			
Х	0.200			
X1	0.450			
X2	0.550			
Y	0.375			
Y1	0.475			
Y2	1.000			

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